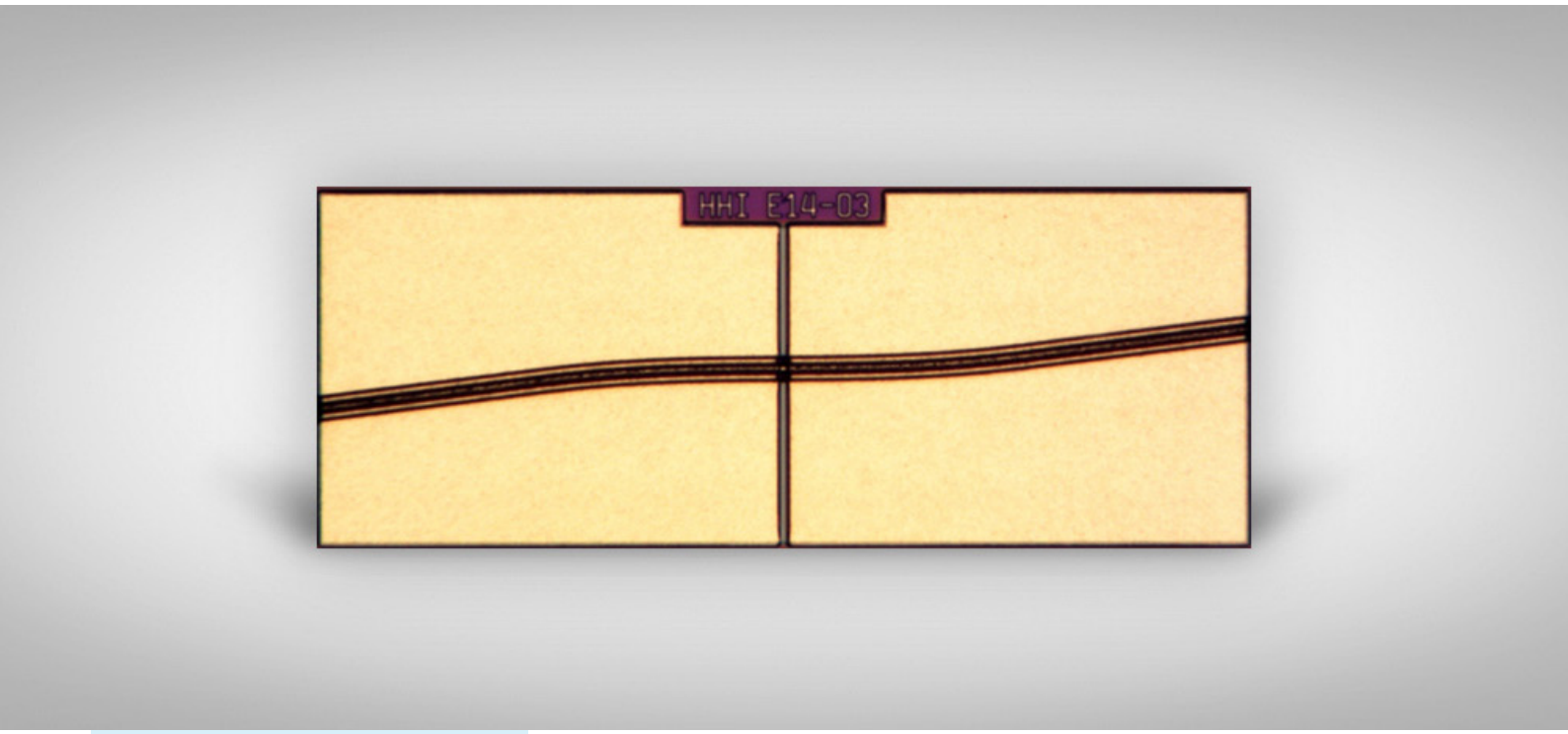
INP-SEMICONDUCTOR OPTICAL AMPLIFIERS

Fraunhofer HHI



AT A GLANCE

High performance o- and c-band InP BH SOAs

Features

- p-side up or flip-chip configuration
- integrated taper for low loss optical coupling
- 7° input/output facet
- circular optical far field, FWHM <20°
- on request precise alignment structures for lateral & vertical positioning
- flexible adaptation of devices corresponding to customer's applications: e.g. center wavelength, polarization sensitivity, coating against n=1.5…

Applications

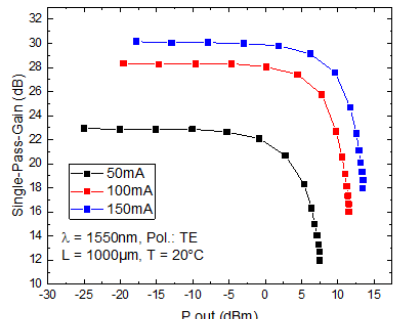
- Telecom/Datacom
- Sensors

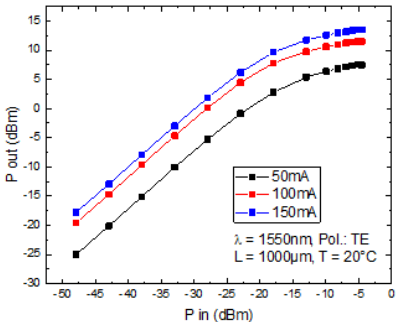
Device variants

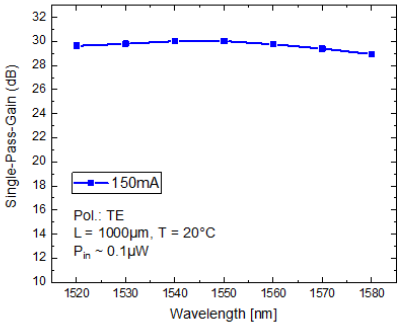
- single chips and arrays

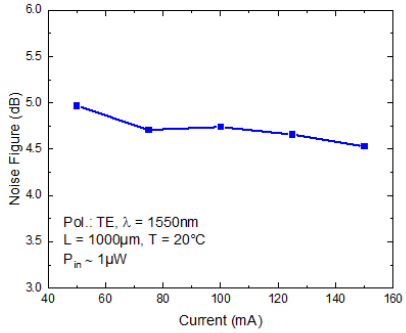
Example: characteristics of c-band SOAs:

Single Pass Gain, output power, spectral bandwidth and noise figure









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